

SWITCHING DIODE

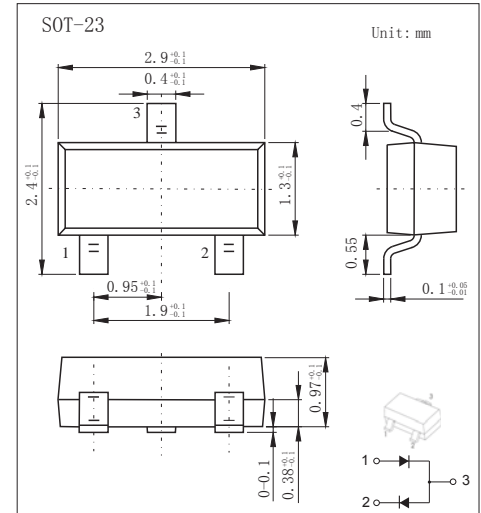
VOLTAGE RANGE: 300V
PEAK PULSE POWER: 250mW

FEATURES

- MMBD2004S type is a silicon switching dual in series diode manufactured by the epitaxial planar process, designed for applications requiring high voltage capability. Power dissipation

MECHANICAL DATA

- Case: SOT-23 Small Outline Plastic Package
- Polarity: Color band denotes cathode end
- Mounting Position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	300	V
DC Blocking Voltage	V_R	240	V
Peak Repetitive Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	625	mA
Forward Surge Current $t=1\mu s$	I_{FSM}	4.0	A
Forward Surge Current $t=1s$	I_{FSM}	1.0	A
Power Dissipation	P_D	250	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55~+150	°C

Electrical Specification ($T_A=25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	240		V
Reverse voltage leakage current	I_R	$V_R=240V$		0.1	μA
Forward voltage	V_F	$I_F=100mA$		1	V
Diode capacitance	C_D	$V_R=0V$ $f=1MHz$		5	pF
Reverses recovery time	t_{rr}	$I_F=I_R=30mA, R_L=100\Omega$		50	ns

MARKING : DB6

RATINGS AND CHARACTERISTIC CURVES

